

Silicon NPN Power Transistors

2SC3577

DESCRIPTION

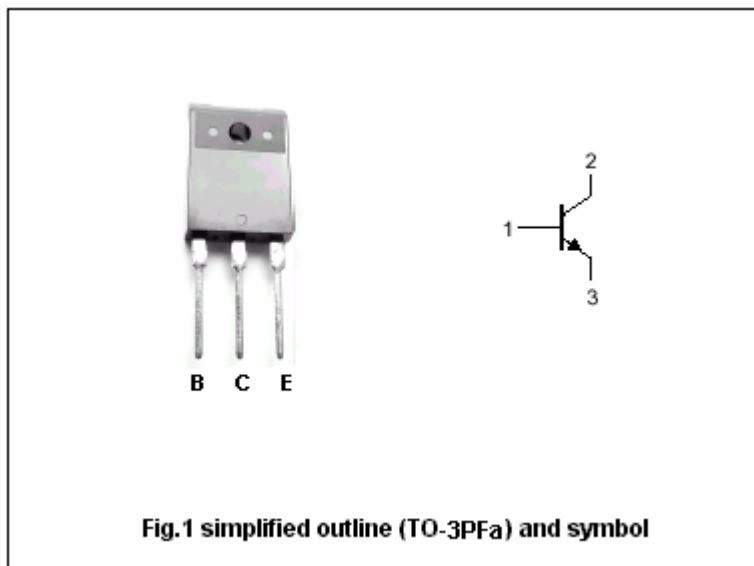
- With TO-3PFa package
- High breakdown voltage
- High speed

APPLICATIONS

- For high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	850	V
V_{CEO}	Collector-emitter voltage	Open base	650	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		10	A
I_B	Base current		3	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	80	W
		$T_a=25^\circ\text{C}$	3	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.5A; L=50mH	650			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A ; I _B =0.6A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A ; I _B =0.6A			1.5	V
I _{CES}	Collector cut-off current	V _{CB} =800V; V _{BE} =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			50	μA
h _{FE-1}	DC current gain	I _C =10mA ; V _{CE} =5V	10			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	6			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		6		MHz

Switching times

t _{on}	Turn-on time	I _C =3A; V _{CC} =250V I _{B1} =0.6A; I _{B2} =-1.2A			1.0	μs
t _{stg}	Storage time				2.5	μs
t _f	Fall time				0.5	μs

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PACKAGE OUTLINE

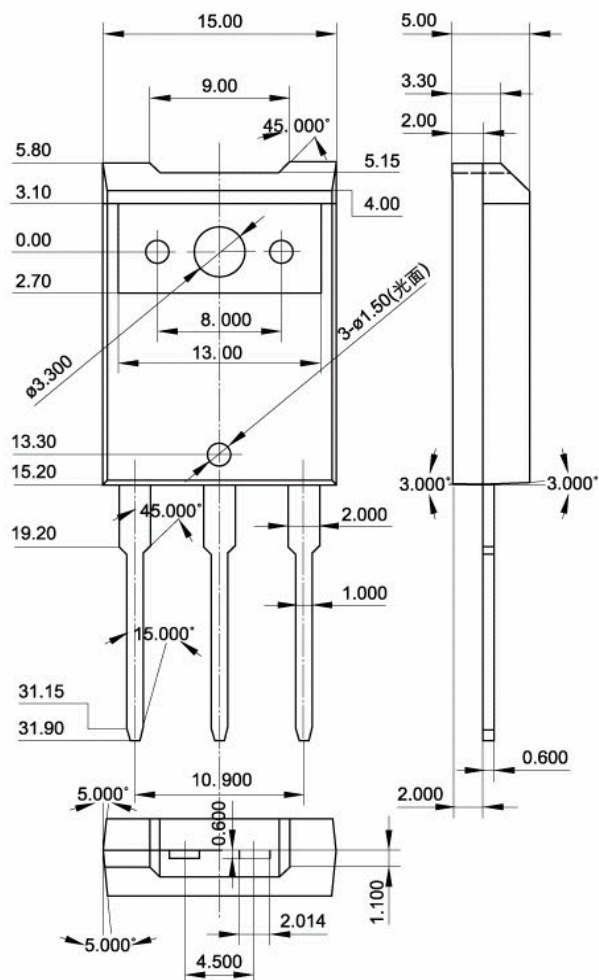


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)